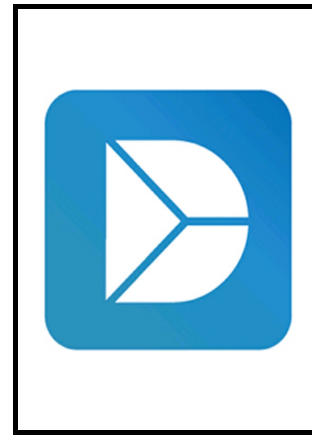


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Data related to the nanoscale structural and compositional evolution in resistance change memories

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*Data related to the nanoscale structural and compositional evolution in resistance change memories*

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**Abstract**

The data included in this article provides additional supplementary information on our recent publication describing “Inducing tunable switching behavior in a single memristor” [1]. Analyses of micro/nano-structural and compositional changes induced in a resistive oxide memory during resistive switching are carried out. Chromium doped strontium titanate based resistance change memories are fabricated in a capacitor-like metal-insulator-metal structure and subjected to different biasing conditions to set memory states. Transmission electron microscope based cross-sectional analyses of the memory devices in different memory states are collected and presented.

**Specifications Table**

Subject area	<i>Electrical Engineering, Material Science</i>
More specific subject area	<i>Resistive oxide memories, Interface engineering</i>
Type of data	<i>Image (Transmission electron microscopy, electron energy loss spectroscopy, energy-dispersive X-ray spectroscopy)</i>
How data was acquired	<i>Cross-sectional lamellae are prepared by focused ion beam (FIB) cuts by</i>

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